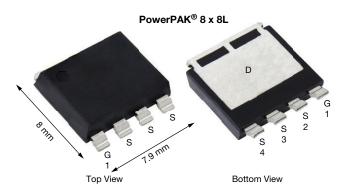
## SQJQ131EL

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**Vishay Siliconix** 

## Automotive P-Channel 30 V (D-S) 175 °C MOSFET

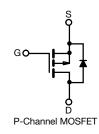


# $\begin{tabular}{|c|c|c|c|} \hline PRODUCT SUMMARY \\ \hline V_{DS} (V) & -30 \\ \hline R_{DS(on)} (\Omega) \mbox{ at } V_{GS} = -10 \ V & 0.0014 \\ \hline I_D (A) & -280 \\ \hline Configuration & Single \\ \hline Package & PowerPAK 8 x 8L \\ \hline \end{tabular}$

#### FEATURES

- AEC-Q101 qualified
- 100 % R<sub>g</sub> and UIS tested
- Thin 1.6 mm package
- · Very low thermal resistance
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





<b>ABSOLUTE MAXIMUM RATINGS</b>	$(T_C = 25 \ ^\circ C, unless)$	s otherwise noted	)			
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-source voltage		V <sub>DS</sub>	-30	V		
Gate-source voltage		V <sub>GS</sub>	±20	V		
Continuous drain current	T <sub>C</sub> = 25 °C	1	-280			
Continuous drain current	T <sub>C</sub> = 125 °C	Ι <sub>D</sub>	-280			
Continuous source current (diode conduction)	۱ <sub>S</sub>	545	А			
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	-280			
Single pulse avalanche current		I <sub>AS</sub>	63			
Single pulse avalanche energy	L = 0.1 IIIH	E <sub>AS</sub>	198	mJ		
Maximum power dissipation	T <sub>C</sub> = 25 °C	P	600	w		
Maximum power dissipation	T <sub>C</sub> = 125 °C	P <sub>D</sub>	200			
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		
Soldering recommendations (peak temperature) d			260			

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount <sup>c</sup>	R <sub>thJA</sub>	44	°C/W		
Junction-to-case (drain)		R <sub>thJC</sub>	0.25	0/10		

Notes

a. Package limited

b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$ 

c. When mounted on 1" square PCB (FR4 material)

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

SQJQ131EL

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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT	
Static	•					•		
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = 250 μA	-30	-	-	v	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μΑ	-1.5	-2	-2.5	v	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, $V_{GS}$ = ± 20 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = -30 V	-	-	1	μA	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -30 V, T <sub>J</sub> = 125 °C	-	-	200		
		$V_{GS} = 0 V$	V <sub>DS</sub> = -30 V, T <sub>J</sub> = 175 °C	-	-	330	1	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V		-100	-	-	Α	
		V <sub>GS</sub> = -4.5 V	V <sub>DS</sub> ≥ -5 V, I <sub>D</sub> = -8 A	-	0.0015	0.0022		
	-	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -10 A	-	0.0010	0.0014		
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -10 A, T <sub>J</sub> = 125 °C	-	-	0.0019	Ω	
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -10 A, T <sub>J</sub> = 175 °C	-	-	0.0022	1	
Forward transconductance b	g <sub>fs</sub>		-15 V, I <sub>D</sub> = -50 A	-	180	-	S	
Dynamic <sup>b</sup>	1	-			1	I		
Input capacitance	C <sub>iss</sub>			-	23 588	33 050		
Output capacitance	Coss	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 15 V, f = 1 MHz	-	2443	3420	pF	
Reverse transfer capacitance	C <sub>rss</sub>			-	2267	3174	1	
Total gate charge <sup>c</sup>	Qq			-	487	731		
Gate-source charge <sup>c</sup>	Q <sub>qs</sub>	V <sub>GS</sub> = 10 V	V <sub>DS</sub> = -15 V, I <sub>D</sub> = -30 A	-	86	-	nC	
Gate-drain charge c	Q <sub>gd</sub>			-	82	-	-	
Gate resistance	R <sub>g</sub>	f = 1 MHz		1	2.1	3.2	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	20	30		
Rise time <sup>c</sup>	t <sub>r</sub>	Vpp =	-15 V, R <sub>I</sub> = 0.5 Ω	-	30	45		
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>		$V_{GEN} = -10 \text{ V}, \text{ R}_{g} = 1 \Omega$	-	194	291	ns	
Fall time <sup>c</sup>	tf			-	78	117	1	
Source-Drain Diode Ratings and Cha	•							
-	ta			20	-	-		
Reverse recovery time	t <sub>b</sub>	1		24	-	-	ns	
	t <sub>rr</sub>	$V_{DD} = -24 \text{ V}, I_{FM} = -20 \text{ A},$		-	43	86		
Reverse recovery charge	Q <sub>rr</sub>	di di	di/dt = 100 A/µs		45	90	nC	
Reverse recovery current	I <sub>RM</sub>	4		-	-	1.9	Α	
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	1100	A	
Forward voltage	V <sub>SD</sub>	I	= -50 A, V <sub>GS</sub> = 0	-	-0.8	-1.1	V	

#### Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

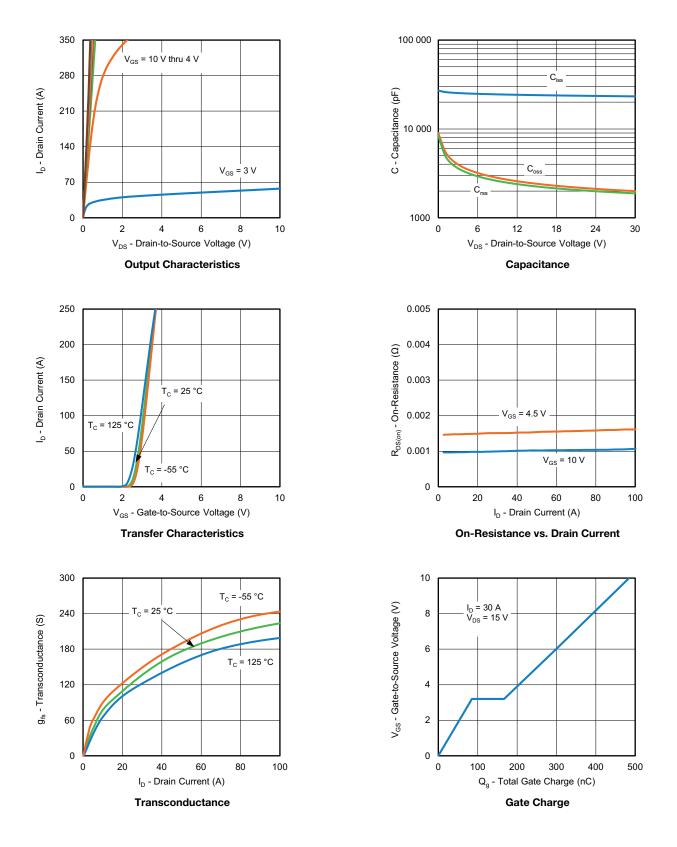
b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



S21-0235-Rev. A, 15-Mar-2021

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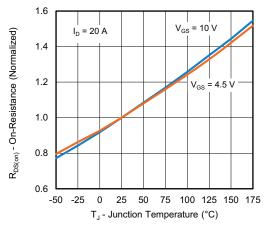
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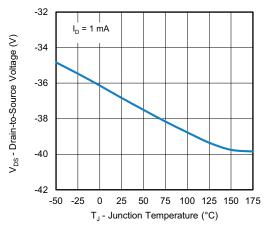
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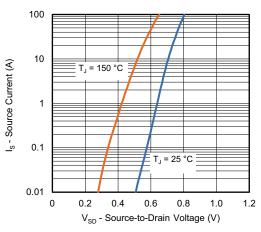
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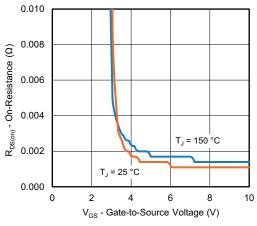
On-Resistance vs. Junction Temperature



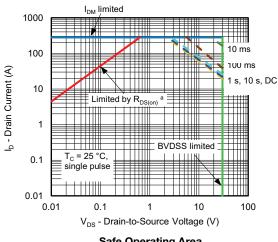
Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage



**On-Resistance vs. Gate-to-Source Voltage** 



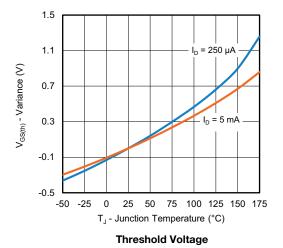
Safe Operating Area

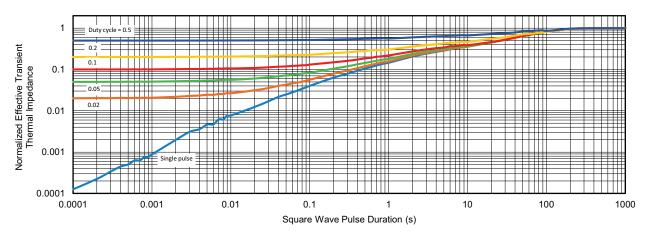
a. V<sub>GS</sub> > minimum V<sub>GS</sub> at which R<sub>DS(on)</sub> is specified

Note

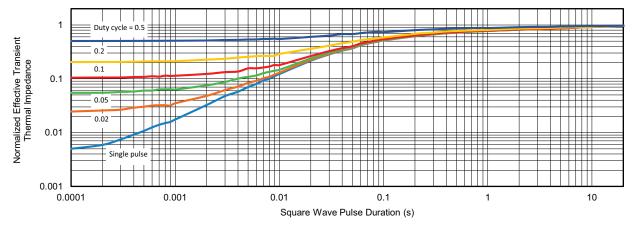


#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

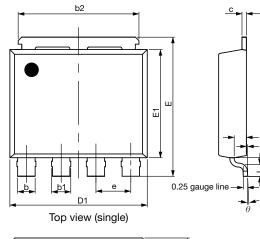
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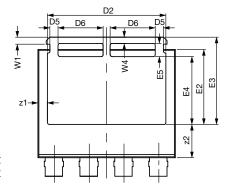
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# PowerPAK<sup>®</sup> 8 x 8L BWL Case Outline 2

A1





Bottom view (single)

1					1	- 4	L
F	-				⇒	∢	
							1
~			 L	 			-

DIM.						
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
А	1.50	1.60	1.70	0.059	0.059 0.063	
A1	0.00	-	0.127	0.000	-	0.005
A2	0.655	0.705	0.755	0.026	0.028	0.030
b	0.92	1.00	1.08	0.036	0.039	0.043
b1	1.02	1.10	1.18	0.040 0.043		0.046
b2	6.84	6.94	7.04	0.269	0.273	0.277
С	0.20	0.25	0.30	0.008	0.010	0.012
D1	7.80	7.90	8.00	0.307	0.311	0.315
D2	6.70	6.80	6.90	0.264	0.268	0.272
D5	0.37	0.47	0.57	0.015	0.019	0.022
D6	2.49	2.59	2.69	0.098	0.102	0.106
е	1.97	2.00	2.03	0.078	0.079	0.080
E	7.90	8.00	8.10	0.311	0.315	0.319
E1	6.12	6.22	6.32	0.241	0.245	0.249
E2	4.21	4.31	4.41	0.166	0.170	0.174
E3	4.92	5.02	5.12	0.194	0.198	0.202
E4	3.80	3.90	4.00	0.150	0.154	0.157
E5	0.65	0.75	0.85	0.026	0.030	0.033
L	0.61	0.68	0.75	0.024	0.027	0.030
L1	1.00	1.07	1.15	0.039	0.042	0.045
W1	0.30	0.40	0.50	0.012	0.016	0.020
W4	0.32	0.37	0.42	0.013	0.015	0.017
z1	0.45	0.55	0.65	0.018	0.022	0.026
z2	1.81	1.91	2.01	0.071	0.075	0.079
θ	0°	-	5°	0°	-	5°

#### Note

Millimeter will govern

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